



No.3571

2SK1433

N-Channel MOS Silicon FET

Very High-Speed Switching Applications

Features

- Low ON-state resistance.
 - Very high-speed switching.
 - Converters.

Absolute Maximum Ratings at Ta = 25°C

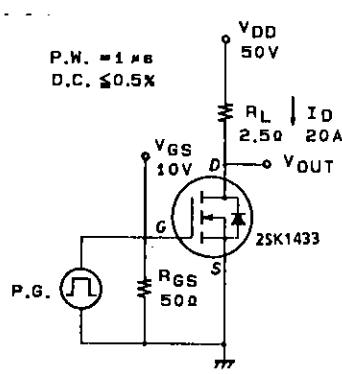
Absolute Maximum Ratings at Ta = 25°C			unit
Drain to Source Voltage	V _{DSS}	100	V
Gate to Source Voltage	V _{GSS}	±20	V
Drain Current(DC)	I _D	30	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10 μs, duty cycle ≤ 1%	120 A
Allowable Power Dissipation	P _D	T _c = 25°C	100 W
			2.5 W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

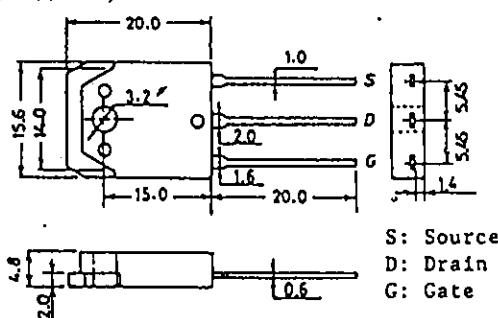
Electrical Characteristics at $T_A = 25^\circ C$			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}, V_{GS} = 0$		100		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0$			100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0$			± 100	nA
Cutoff Voltage	$V_{GS(\text{off})}$	$V_{DS} = 10V, I_D = 1\text{mA}$		1.5	2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, I_D = 20\text{A}$	13	22		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = 20\text{A}, V_{GS} = 10V$		0.040	0.055	Ω
Input Capacitance	C_{iss}	$V_{DS} = 20V, f = 1\text{MHz}$		2400		pF
Output Capacitance	C_{oss}	$V_{DS} = 20V, f = 1\text{MHz}$		700		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 20V, f = 1\text{MHz}$		200		pF
Turn-ON Delay Time	$t_{d(on)}$			30		ns
Rise Time	t_r	$I_D = 20\text{A}, V_{GS} = 10V$		90		ns
Turn-OFF Delay Time	$t_{d(off)}$	$V_{DD} = 50V, R_{GS} = 50\Omega$		320		ns
Fall Time	t_f			130		ns
Diode Forward Voltage	V_{SD}	$I_S = 30\text{A}, V_{GS} = 0$		1.8		V

(Note) Be careful in handling the 2SK1433 because it has no protection diode between gate and source.

Switching Time Test Circuit

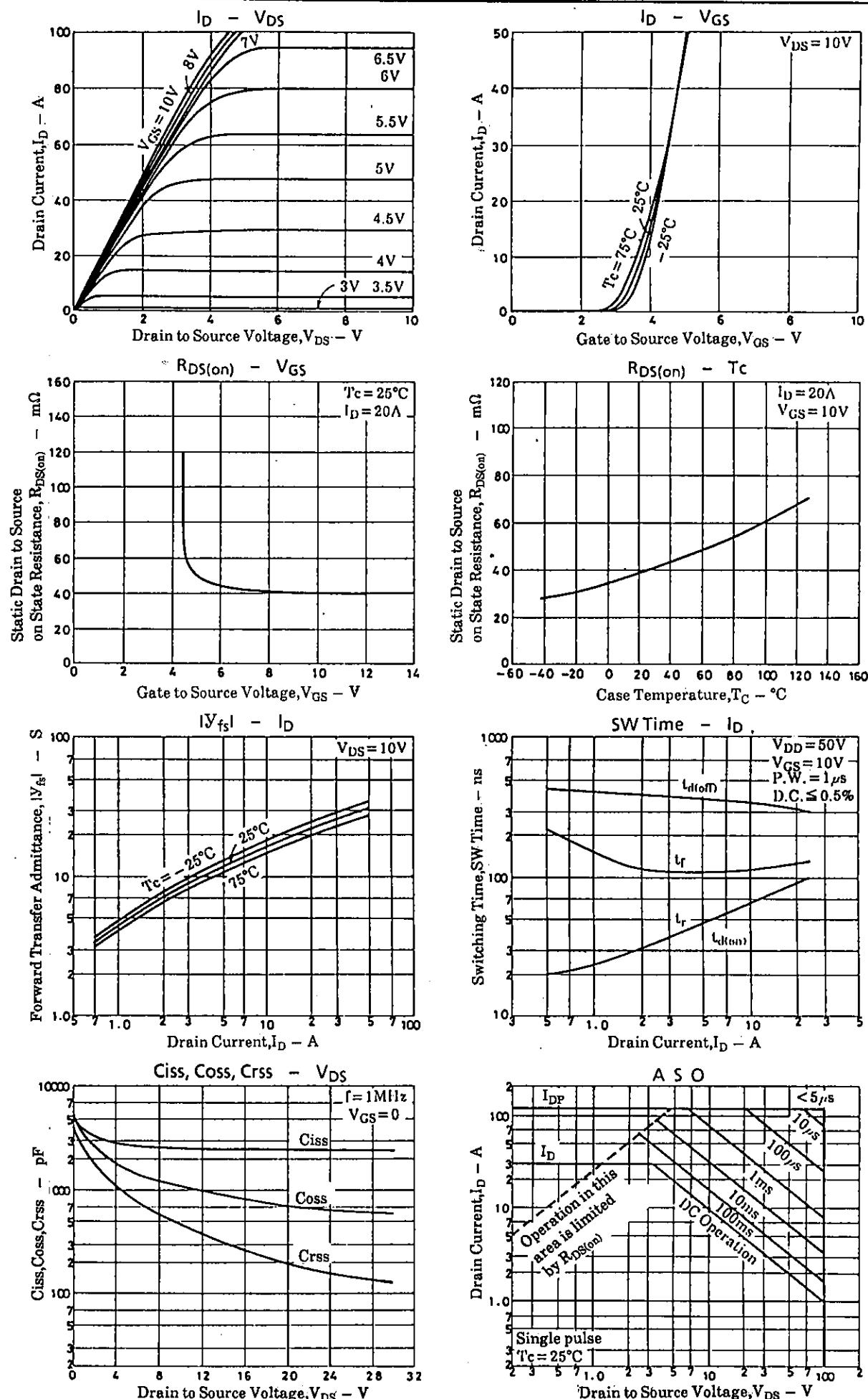


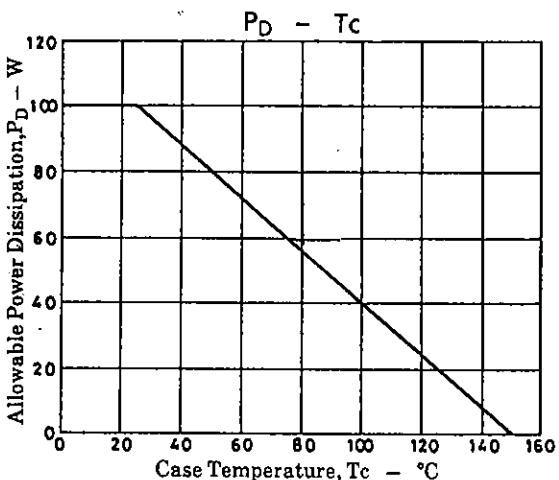
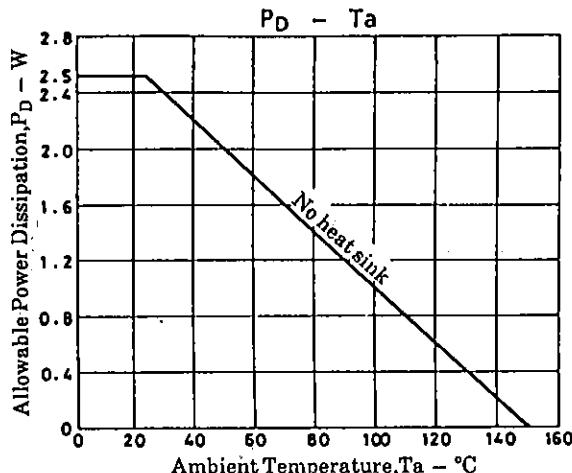
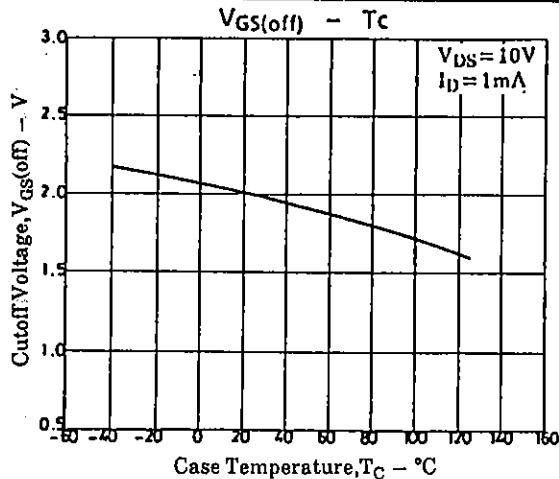
Package Dimensions 2056 (unit : mm)



SANYO: TO3PB

SANYO Electric Co.,Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN





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